

**UNITED STATES DEPARTMENT OF COMMERCE****Patent and Trademark Office**

Address: COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, D.C. 20231

AJ

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.
-----------------	-------------	----------------------	---------------------

08/825,360 03/28/97 LIAO

M 761/P7US/CVD

MMC:2/0926

EXAMINER

PATENT COUNSEL
APPLIED MATERIALS INC
3050 BOWERS AVENUE
PO BOX 450A
SANTA CLARA CA 95052

QUACH, T

ART UNIT	PAPER NUMBER
----------	--------------

2814

DATE MAILED: 09/26/00

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner of Patents and Trademarks

Office Action Summary

Application No. 08/825,360	Applicant(s) Liao et al.
Examiner Quach, T.	Group Art Unit 2814



Responsive to communication(s) filed on Jun 30, 2000

This action is **FINAL**.

Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11; 453 O.G. 213.

A shortened statutory period for response to this action is set to expire three month(s), or thirty days, whichever is longer, from the mailing date of this communication. Failure to respond within the period for response will cause the application to become abandoned. (35 U.S.C. § 133). Extensions of time may be obtained under the provisions of 37 CFR 1.136(a).

Disposition of Claims

Claim(s) 21-53 is/are pending in the application.

Of the above, claim(s) _____ is/are withdrawn from consideration.

Claim(s) _____ is/are allowed.

Claim(s) 21-53 is/are rejected.

Claim(s) _____ is/are objected to.

Claims _____ are subject to restriction or election requirement.

Application Papers

See the attached Notice of Draftsperson's Patent Drawing Review, PTO-948.

The drawing(s) filed on _____ is/are objected to by the Examiner.

The proposed drawing correction, filed on _____ is approved disapproved.

The specification is objected to by the Examiner.

The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. § 119

Acknowledgement is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d).

All Some* None of the CERTIFIED copies of the priority documents have been

received.

received in Application No. (Series Code/Serial Number) _____.

received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

*Certified copies not received: _____

Acknowledgement is made of a claim for domestic priority under 35 U.S.C. § 119(e).

Attachment(s)

Notice of References Cited, PTO-892

Information Disclosure Statement(s), PTO-1449, Paper No(s). and 14 & 18

Interview Summary, PTO-413

Notice of Draftsperson's Patent Drawing Review, PTO-948

Notice of Informal Patent Application, PTO-152

--- SEE OFFICE ACTION ON THE FOLLOWING PAGES ---

Art Unit: 2814

DETAILED ACTION

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(f) or (g) prior art under 35 U.S.C. 103(a).

Claims 21-23 and 40-45 are rejected under 35 U.S.C. 102(e) as anticipated by or, in the alternative, under 35 U.S.C. 103(a) as obvious over Bai et al.

Art Unit: 2814

Bai et al. teach forming substrate 40, forming dielectric 41, patterning the dielectric layer to form trench 47, forming capturing layer 43 of titanium material having thickness between 5Å and 500Å, forming blocking layer of titanium nitride having thickness between 10Å and 500Å.

See column 5 lines 1-33, column 8 lines 7-57, Fig. 3 to 10 lines 4-49.

Note that the inventive feature of the capturing layer, the blocking layer, the refractory metal, the refractory metal nitride, and the layer thicknesses as characterized correspond to the claimed invention in claims 1-20 of Bai et al., column 10 line 5 to column 12 line 32, e.g., claim 1 line 4-11, claim 3 line 3, claim 4 line 3, claim 9 lines 1-4, claim 10 lines 4-12, claim 11 line 3-5, claim 16 lines 1-13, claim 17 line 3, claim 18 line 3, claims 19 and 20 lines 1-4.

The claimed parameters, e.g., thickness of less than 130Å, width less than 3000 Å, aspect ratios greater than 3.33 is anticipated given the range taught in Bai et al. Any range and combined range claimed not anticipated by Bai et al. would have been obvious to one skilled in the art given the teaching of Bai et al., e.g., column 5 lines 6 et seq., to optimize the barrier thickness to obtain the desired resistance of the interconnect. Any parameters not anticipated are deemed to have been obvious and would have been within the purview of one skilled in the art to obtain the desired trench width and aspect ratio.

The Bai et al reference is a U.S. patent that claims the rejected invention. An affidavit or declaration is inappropriate under 37 CFR 1.131(a) when the patent is claiming the same patentable invention, see MPEP § 2306. The patent can only be overcome by establishing priority

Art Unit: 2814

of invention through interference proceedings. See MPEP Chapter 2300 for information on initiating interference proceedings.

Claims 24-31, 48-50, 52, and 53 are rejected under 35 U.S.C. 103(a) as being unpatentable over Bai et al. as applied to claims 21-23 and 40-45 above, and further in view of Ho et al., Hower et al., and Fu et al.

The reference as applied above does not recite plasma annealing of the titanium nitride barrier layer.

Ho et al. teach plasma reaction of titanium nitride in suitable gases, e.g., oxygen, nitrogen, to fill the grain boundaries hence improving barrier characteristics. See column 7 line 28 to column 8. The use of nitrogen or hydrogen as the gas to stuff the nitrogen is also taught. See column 7 lines 4-27, column 10 lines 3-20.

Hower et al. teach plasma treatment of titanium nitride to reduce silicon movement therethrough and to reduce interface defects. See column 2 line 56 to column 3 line 28 to column 3 line 30.

Fu et al. teach plasma treatment of titanium nitride in argon wherein the treatment smooths the TiN surface and improves wettability. See column 2 line 48 to column 3 line 16.

It would have been obvious to one skilled in the art at the time the invention was made in practicing the Bai et al. process to have employed plasma treatment of the titanium nitride since such is conventional and advantageous to improve barrier characteristics and wettability as taught by Ho et al., Hower et al., and Fu et al. It would have been obvious and would have been within

Art Unit: 2814

the purview of one skilled in the art to have selected the desired conventional plasmas, the conventional electrical biasing and rf signal, to have employed single chamber for deposition and annealing, and to employ conventional alternative metal nitrides. Alternatively, official notice is given regarding any conventional plasmas, alternative metal nitrides enumerated in the claims that are not recited above and the use of electrical biasing and rf signal as claimed.

Claims 32-39 and 51 are rejected under 35 U.S.C. 103(a) as being unpatentable over Bai et al. and further in view of Ho et al., Hower et al., and Fu et al.

The references are applied as above. Note further that Ho et al. teach the use of two anneals, e.g., first anneal of nitrogen and second anneal of hydrogen. See e.g., column 7 lines 4-27, column 10 lines 8-20.

It would have been obvious to one skilled in the art at the time the invention was made in practicing the above process to have employed two plasma anneals since such would permit the stuffing of the gases in the titanium nitride to improve barrier characteristics. The use of gas plasma is conventional and advantageous wherein the plasma would increase the stuffing in the barrier material.

Claims 46-47 are rejected under 35 U.S.C. 103(a) as being unpatentable over Bai et al. as applied to claims 21-23, 40-45 above, and further in view of Dixit et al.

The reference as applied above does not recite the upper metallization layer of tungsten.

Art Unit: 2814

Dixit et al. teach the filling of tungsten on the titanium/titanium nitride to complete interconnection having low resistivity. See column 5 lines 3-57, column 7 lines 34 to column 8 line 13.

It would have been obvious to one skilled in the art at the time the invention was made in practicing the above process to have employed tungsten as interconnection since such is conventional and advantageous as taught in Dixit et al.

Claims 21-23 and 40-47 are rejected under 35 U.S.C. 103(a) as being unpatentable over Dixit et al. or Sandhu et al. taken with Suguro et al.

Dixit et al. teach forming channels 16 through insulating layer 14, forming titanium 18 e.g., about 100 angstroms, forming titanium nitride thereon, e.g., to about 250 angstroms using conventional deposition method. Well known alternative refractory metals and metal nitrides and alternative deposition techniques are also shown. Subsequent formation of metallization such as tungsten and etchback is also taught. See column 4 line 64 to column 7 line 11.

Sandhu et al. also teach forming channels 31 in insulating layer 32, forming titanium layer 35, forming titanium nitride barrier layer 41, forming tungsten or aluminum or copper thereon. See column 6 line 61 to column 7 line 33.

Thus Dixit et al. or Sandhu et al. lack anticipation in that the metal nitride having thickness or less than 130 angstroms is not taught. Dixit et al. employ the preferred thickness of 250 angstroms for the barrier nitride.

Art Unit: 2814

Suguro et al. teach the use of TiN as barrier layer wherein optimization of layer thickness of the titanium nitride is also taught, including the use of TiN thickness of 4 nm, 7 nm, and 10 nm, see the abstract, the paragraph bridging page 280 and 281, wherein TiN thickness as low as 10 nm was employed.

It would have been obvious to one skilled in the art in practicing Dixit et al. or Sandhu et al. to have selected the desired thickness of the nitride barrier layer since such thickness variation and optimization is well within the purview of one skilled in the art as evidenced by Suguro et al., including the selection of the thickness claimed of less than 13 nm, given the thicknesses taught by Suguro et al. The claimed parameters, e.g., thickness of less than 130Å, thus would have been obvious given the range taught in Suguro et al. The use of thin adhesion layer employing conventional processing would have been obvious given the teaching of Dixit et al. wherein such thickness optimization would have been obvious and would have been within the purview of one skilled in the art. The use of alternative refractory metals and metal nitrides, of conventional deposition methods, would have been obvious and would correspond to obvious alternative materials and deposition and planarization process and as such would have been within the purview of one skilled in the art. The selection of high aspect ratio and reduced submicron trench width and of etchback of the respective layers to the extent desired to form plugs employing conventional processing is well known in the art and is well within the purview of one skilled in the art and as such would have been obvious.

Art Unit: 2814

Claims 24-31, 48-50, 52, and 53 are rejected under 35 U.S.C. 103(a) as being unpatentable over Dixit et al. or Sandhu et al. taken with Suguro et al. as applied to claims 21-23 and 40-47 above, and further in view of Ho et al., Hower et al., and Fu et al.

The reference as applied above does not recite plasma annealing of the titanium nitride barrier layer.

Ho et al. teach plasma reaction of titanium nitride in suitable gases, e.g., oxygen, nitrogen, to fill the grain boundaries hence improving barrier characteristics. See column 7 line 28 to column 8. The use of nitrogen or hydrogen as the gas to stuff the nitrogen is also taught. See column 7 lines 4-27, column 10 lines 3-20.

Hower et al. teach plasma treatment of titanium nitride to reduce silicon movement therethrough and to reduce interface defects. See column 2 line 56 to column 3 line 28 to column 3 line 30.

Fu et al. teach plasma treatment of titanium nitride in argon wherein the treatment smooths the TiN surface and improves wettability. See column 2 line 48 to column 3 line 16.

The reasons applied to claims 21-23 and 40-47 apply, and additionally, it would have been obvious to one skilled in the art at the time the invention was made in practicing the above process to have employed plasma treatment of the titanium nitride since such is conventional and advantageous to improve barrier characteristics and wettability as taught by Ho et al., Hower et al., and Fu et al. It would have been obvious and would have been within the purview of one skilled in the art to have selected the desired conventional plasmas, the conventional electrical

Art Unit: 2814

biasing and rf signal, to have employed single chamber for deposition and annealing, and to employ conventional alternative metal nitrides. Alternatively, official notice is given regarding any conventional plasmas, alternative metal nitrides enumerated in the claims that are not recited above and the use of electrical biasing and rf signal as claimed.

Claims 32-39 and 51 are rejected under 35 U.S.C. 103(a) as being unpatentable over Dixit et al. or Sandhu et al. taken with Suguro et al. and further in view of Ho et al., Hower et al., and Fu et al.

The references are applied as above. Note further that Ho et al. teach the use of two anneals, e.g., first anneal of nitrogen and second anneal of hydrogen. See e.g., column 7 lines 4-27, column 10 lines 8-20.

It would have been obvious to one skilled in the art at the time the invention was made in practicing the above process to have employed two plasma anneals since such would permit the stuffing of the gases in the titanium nitride to improve barrier characteristics. The use of gas plasma is conventional and advantageous wherein the plasma would increase the stuffing in the barrier material.

Applicant's arguments filed June 30, 2000 have been fully considered but they are not persuasive.

Initially, applicant alleges that the Declaration pursuant to 37 CFR 1.131 is sufficient to establish an earlier invention date over the Bai et al. reference. Nonetheless, the Bai et al.

Art Unit: 2814

reference is a U.S. patent that claims the rejected invention. Accordingly, the declaration is inappropriate when the patent is claiming the same patentable invention, see MPEP § 2306.

Applicant alleges that Dixit et al. teach away from the instant application in that the TiN employed must be a minimumn 250 Å. This nonetheless overlooks the teachings of Suguro et al. wherein the optimization of layer thickness of TiN as barrier layer is clearly shown, including the use of TiN thickness of 4nm, 7 nm, and 10 nm (which correspond to 40 Å, 70 Å, and 100 Å, respectively), see, e.g., the abstract, page 277, and the paragraph bridging pages 280 and 2810 wherein the optimization of TiN layer thickness is explicitly contemplated, including the thickness of about 10 nm for optimal barrier function.

Applicant alleges that Suguro et al. do not look at interconnection structure. Nonetheless, Suguro et al. clearly contemplate such barrier in metallization schemes. See page 277 left column, page 278, first full paragraph. It remains apparent to one skilled in the art that such application to metallization structures would have been apparent to one skilled in the art.

Applicant also alleges that the Suguro reference does not appear to be of record on an initialized form PTO 1449 and requested such form. Nonetheless, such reference was already made of record on the PTO 892 of record accompanied the Office action mailed December 30, 1999. An extra copy of said PTO 892 is provided with this Office action.

THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

Art Unit: 2814

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to examiner Quach whose telephone number is (703) 308-1096. The examiner can normally be reached on Monday through Friday from 8:30 to 5.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri, can be reached on (703) 306-2794. The fax phone number for the organization where this application or proceeding is assigned is (703) 308-7722 or (703) 308-7724.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.



Tuan Quach
Primary Examiner